

#### **Features**

- Trench Power LV MOSFET Technology
- · Excellent Package for Heat Dissipation
- High Density Cell Design for Low R<sub>DS(on)</sub>
- Epoxy Meets UL 94 V-0 Flammability Rating
- · Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

### **Maximum Ratings**

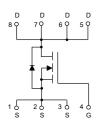
- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance: 5°C/W Junction to Case<sup>(Note 2)</sup>

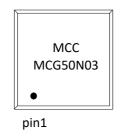
Parameter	Symbol	Rating	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Volltage		V <sub>GS</sub>	±20	V
Continuous Drain Current	T <sub>C</sub> =25°C		50	Α
	T <sub>C</sub> =100°C	- I <sub>D</sub>	35	Α
Pulsed Drain Current (Note 3)		I <sub>DM</sub>	190	Α
Single Pulse Avalanche Energy (Note 4)		E <sub>AS</sub>	225	mJ
Total Power Dissipation	T <sub>C</sub> =25°C	- P <sub>D</sub>	30	W
	T <sub>C</sub> =100°C	] 'D	15	W

#### Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2.  $R_{\theta JA}$  is the Sum of the Junction-to-Case and Case-to-Ambient Thermal Resistance, Where the Case Thermal Reference is Defined as The Solder Mounting Surface of the Drain Pins.  $R_{\theta JC}$  is Guaranteed by Design, While  $R_{\theta JA}$  is Determined by the Board Design. The Maximum Rating Presented Here is Based on Mounting on a 1 in<sup>2</sup> pad of 2oz Copper.
- 3. Pulse Test; Pulse Width≤300µs, Duty Cycle ≤2%.
- 4.  $T_J$ =25°C,  $V_{DS}$ =30V,  $V_{DD}$ =25V,  $V_{GS}$ =10V, L=1mH.

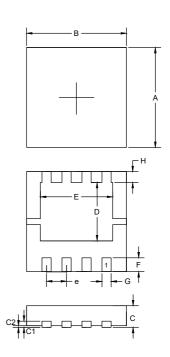
## **Internal Structure and Marking Code**





# N-CHANNEL MOSFET

#### **DFN3333**



DIMENSIONS					
DIM INC		HES	М	М	NOTE
וווט	MIN	MAX	MIN	MAX	NOTE
Α	0.126	0.130	3.20	3.30	
В	0.126	0.130	3.20	3.30	
С	0.030	0.033	0.75	0.85	
C1	0.007	0.009	0.18	0.22	
C2		0.002		0.05	
D	0.071	0.079	1.80	2.00	
Е	0.087	0.098	2.20	2.50	
F	0.016	0.020	0.40	0.50	
G	0.010	0.014	0.25	0.35	
Н	0.012	0.016	0.30	0.40	
е	0.024	0.028	0.60	0.70	

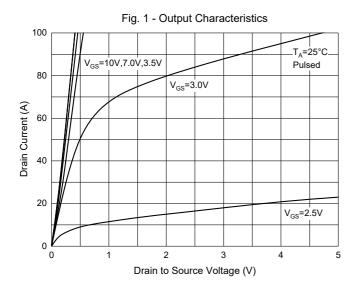


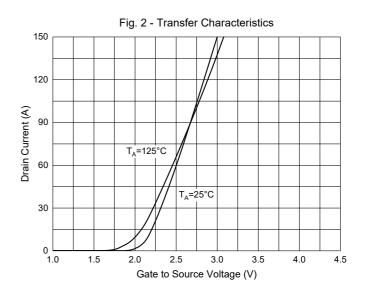
## Electrical Characteristics @ 25°C (Unless Otherwise Specified)

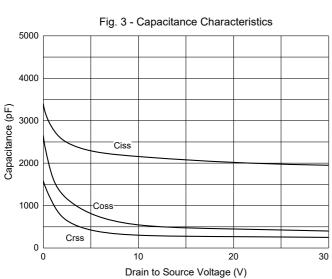
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Characteristics	-	,				
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30			V
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1	1.5	2.5	V
Drain-Source On-Resistance		V <sub>GS</sub> =10V, I <sub>D</sub> =15A	4.9 6		6	
	$R_{DS(on)}$	V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A		6.3	8	– mΩ
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A			1.2	V
Continuous Body Diode Current	Is				50	Α
Dynamic Characteristics						
Input Capacitance	C <sub>iss</sub>			2150		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V,f=1MHz		435		
Reverse Transfer Capacitance	C <sub>rss</sub>			252		
Total Gate Charge	$Q_g$			52.8		nC
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =15V,V <sub>GS</sub> =10V,I <sub>D</sub> =20A		12.3		
Gate-Drain Charge	$Q_{gd}$			10.8		
Turn-On Delay Time	t <sub>d(on)</sub>			9		- ns
Turn-On Rise Time	t <sub>r</sub>	$V_{GS}$ =10V, $V_{DD}$ =20V, $I_{D}$ =4A, $R_{L}$ =1 $\Omega$ $R_{GEN}$ =3 $\Omega$		15.5		
Turn-Off Delay Time	t <sub>d(off)</sub>			29		
Turn-Off Fall Time	t <sub>f</sub>			9		
Reverse Recovery Chrage	Qrr	L = 25 A di/dt= 100 A /u.s		28		nC
Reverse Recovery Time	trr	I <sub>F</sub> =25A, di/dt=100A/μs		27		ns

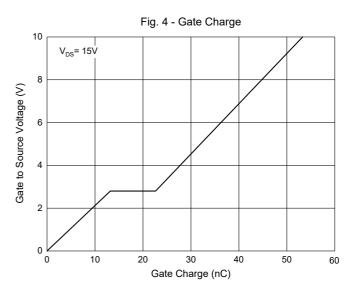


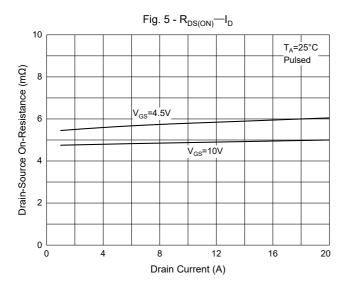
#### **Curve Characteristics**

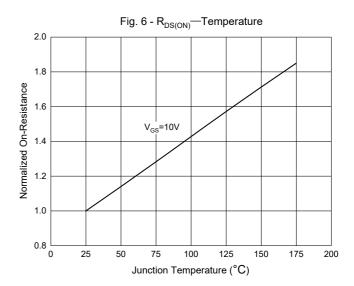






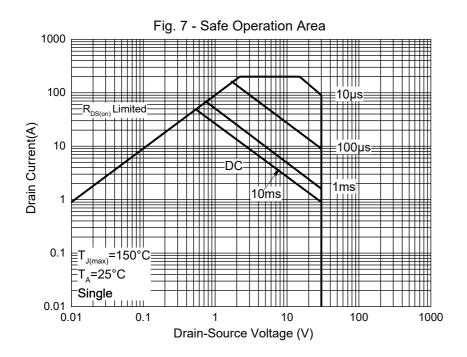


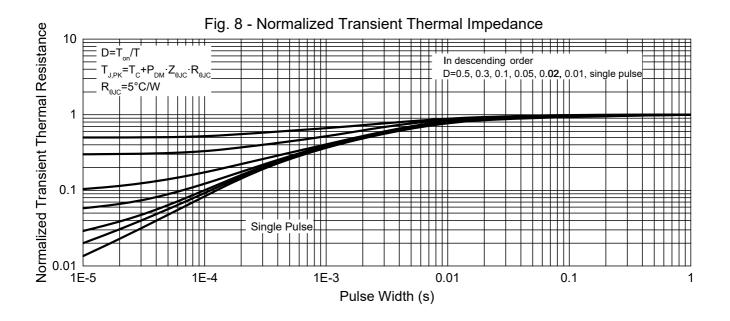






#### **Curve Characteristics**







#### **Ordering Information**

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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